Amendments to the Claims:

Claims 1-19 have been canceled. New claims 20-31 are added. Please note that all claims currently pending and under consideration in the referenced application are shown below. Please enter these claims as amended. This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

Claims 1-19 canceled.

20. (New) A method of forming an opening in a borophosphosilicate glass layer on a semiconductor device, the method comprising:

providing a layer of borophosphosilicate glass over a layer of tetraethyl orthosilicate;

masking a pattern on the borophosphosilicate glass layer; and

etching the borophosphosilicate glass layer with an etchant comprising organic acid and a fluoride-containing.

21. (New) The method of claim 20, wherein the organic acid is selected from the group consisting of acetic acid, formic acid and oxalic acid.

22. (New) The method of claim 20, wherein the fluoride-containing solution is selected from the group consisting of hydrofluoric acid and ammonium fluoride.

21. (New) The method of claim 20, wherein the organic acid comprises 99.7% acetic acid by weight in water and the fluoride-containing solution comprises 49% hydrofluoric acid by weight in water.

22. (New) The method of claim 21, wherein the acetic acid is in a volumetric ratio with the hydrofluoric acid from between about 1:1 to 500:1.

23. (New) The method of claim 22, wherein the acetic acid is in a volumetric ratio with the hydrofluoric acid at about 10:1 to about 100:1.

24. (New) The method of claim 20, wherein the organic acid comprises 99.7% acetic acid by weight in water and the fluoride-containing solution comprises 40% ammonium fluoride acid by weight in water.

25. (New) The method of claim 20, wherein the etchant includes a selectivity ratio of borophosphosilicate glass to tetraethyl orthosilicate between about 27:1 and 55:1.

26. (New) A method of selectively etching a borophosphosilicate glass layer on a semiconductor device, the method comprising:

providing a semiconductor substrate having a layer of layer of tetraethyl orthosilicate and an overlying layer of borophosphosilicate glass; and

contacting the borophosphosilicate glass layer with a solution comprising organic acid and a fluoride-containing.

27. (New) The method of claim 26, wherein the organic acid comprises 99.7% acetic acid by weight in water and the fluoride-containing solution comprises 49% hydrofluoric acid by weight in water.

28. (New) The method of claim 27, wherein the acetic acid is in a volumetric ratio with the hydrofluoric acid from between about 1:1 to 500:1.

29. (New) The method of claim 28, wherein the acetic acid is in a volumetric ratio with the hydrofluoric acid at about 10:1 to about 100:1.

30. (New) The method of claim 26, wherein the organic acid comprises 99.7% acetic acid by weight in water and the fluoride-containing solution comprises 40% ammonium fluoride acid by weight in water.

31. (New) The method of claim 26, wherein the solution includes a selectivity ratio of borophosphosilicate glass to tetraethyl orthosilicate between about 27:1 and 55:1.